

forming a first metal electrode film, an inorganic high dielectric film and a second metal electrode film in this order on the metal oxide adhesive film, using respective masks;

wherein the first metal electrode film, the inorganic high dielectric film and the second metal dielectric film are formed in contact with the metal oxide adhesive film, thereby being integrated with the substrate by the metal oxide adhesive film.

B1
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17. (Amended) The method for producing a flexible thin film capacitor according to claim 15, wherein a metal adhesive film is formed in a region where the first metal electrode film is to be formed on the metal oxide adhesive film.

B2

22. (Amended) The method for producing a flexible thin film capacitor according to claim 15, wherein the metal oxide adhesive film is formed by at least one method selected from the group consisting of RF magnetron sputtering, ECR magnetron sputtering, a vacuum evaporation method, a CVD method and a sol-gel process.

B3

23. (Amended) The method for producing a flexible thin film capacitor according to claim 15, wherein the metal oxide adhesive film is formed by treating a metal film with a solution, and the metal film is formed by at least one method selected from the group consisting of DC magnetron sputtering, RF magnetron sputtering, ECR magnetron sputtering, a CVD method and a vacuum evaporation method.